### **INTEGRATED CIRCUITS**

# DATA SHEET

# 74HC1G08; 74HCT1G08 2-input AND gate

Product specification Supersedes data of 2001 Mar 02 2002 May 17





### 2-input AND gate

### 74HC1G08; 74HCT1G08

#### **FEATURES**

- Wide supply voltage range from 2.0 to 6.0 V
- · Symmetrical output impedance
- · High noise immunity
- · Low power dissipation
- Balanced propagation delays
- Very small 5 pins package
- · Output capability: standard.

### **DESCRIPTION**

The 74HC1G/HCT1G08 is a high-speed Si-gate CMOS device.

The 74HC1G/HCT1G08 provides the 2-input AND function. The standard output currents are  $\frac{1}{2}$  compared to the 74HC/HCT08.

#### **QUICK REFERENCE DATA**

GND = 0 V;  $T_{amb}$  = 25 °C;  $t_r$  =  $t_f \le 6.0$  ns.

SYMBOL	PARAMETER	CONDITIONS	TYP	UNIT	
STWIDOL	I ANAIVIL I EN	CONDITIONS	HC1G	HCT1G	ONII
t <sub>PHL</sub> /t <sub>PLH</sub>	propagation delay A and B to Y	C <sub>L</sub> = 15 pF; V <sub>CC</sub> = 5 V	7	11	ns
Cı	input capacitance		1.5	1.5	pF
C <sub>PD</sub>	power dissipation capacitance	notes 1 and 2	19	21	pF

#### **Notes**

1.  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$$
 where:

 $f_i$  = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in Volts;

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$ 

2. For HC1G the condition is  $V_I = GND$  to  $V_{CC}$ .

For HCT1G the condition is  $V_I = GND$  to  $V_{CC} - 1.5 V$ .

### **FUNCTION TABLE**

See note 1.

INP	INPUTS					
Α	В	Y				
L	L	L				
L	Н	L				
Н	L	L				
Н	Н	Н				

### Note

- 1. H = HIGH voltage level;
  - L = LOW voltage level.

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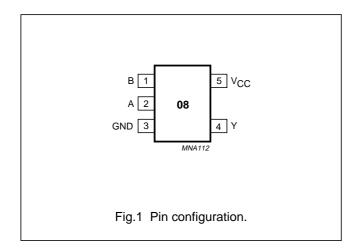
### **ORDERING INFORMATION**

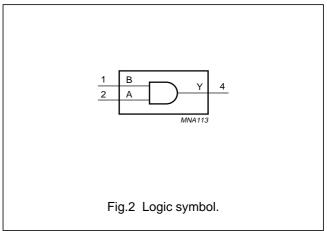
	PACKAGE									
TYPE NUMBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING				
74HC1G08GW	–40 to +125 °C	5	SC-88A	plastic	SOT353	HE				
74HCT1G08GW	-40 to +125 °C	5	SC-88A	plastic	SOT353	TE				
74HC1G08GV	-40 to +125 °C	5	SC-74A	plastic	SOT753	H08				
74HCT1G08GV	-40 to +125 °C	5	SC-74A	plastic	SOT753	T08				

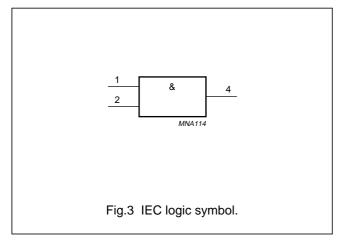
### **PINNING**

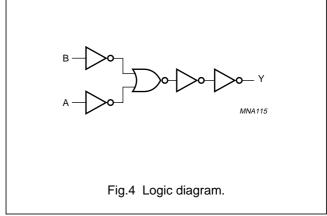
PIN	SYMBOL	DESCRIPTION
1	В	data input B
2	А	data input A
3	GND	ground (0 V)
4	Υ	data output Y
5	V <sub>CC</sub>	supply voltage

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### **RECOMMENDED OPERATING CONDITIONS**

CVMBOL	PARAMETER	CONDITIONS	7	4HC1G0	)4	74	UNIT		
SYMBOL		CONDITIONS	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNII
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	_	V <sub>CC</sub>	0	_	V <sub>CC</sub>	V
Vo	output voltage		0	_	V <sub>CC</sub>	0	_	V <sub>CC</sub>	V
T <sub>amb</sub>	operating ambient temperature	see DC and AC characteristics per device	-40	+25	+125	-40	+25	+125	°C
t <sub>r</sub> , t <sub>f</sub>	input rise and fall times	V <sub>CC</sub> = 2.0 V	_	_	1000	_	_	_	ns
		V <sub>CC</sub> = 4.5 V	_	_	500	_	_	500	ns
		V <sub>CC</sub> = 6.0 V	_	_	400	_	_	_	ns

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input diode current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}; \text{ note 1}$	_	±20	mA
I <sub>OK</sub>	output diode current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}; \text{ note 1}$	_	±20	mA
Io	output source or sink current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$ ; note 1	_	±12.5	mA
I <sub>CC</sub>	V <sub>CC</sub> or GND current	note 1	_	±25	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>D</sub>	power dissipation per package	for temperature range from –40 to +125 °C; note 2	_	200	mW

### **Notes**

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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2. Above 55  $^{\circ}\text{C}$  the value of  $P_D$  derates linearly with 2.5 mW/K.

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### **DC CHARACTERISTICS**

### Family 74HC1G

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

		TEST CONDIT	IONS			T <sub>amb</sub> (°C	)		
SYMBOL	PARAMETER	O.T.I.E.D.			-40 to +8	5	−40 t	o +125	UNIT
		OTHER V <sub>CC</sub> (V)		MIN.	<b>TYP.</b> <sup>(1)</sup>	MAX.	MIN.	MAX.	1
V <sub>IH</sub>	HIGH-level input voltage		2.0	1.5	1.2	_	1.5	_	V
			4.5	3.15	2.4	_	3.15	-	V
			6.0	4.2	3.2	_	4.2	_	V
V <sub>IL</sub>	LOW-level input voltage		2.0	_	0.8	0.5	_	0.5	V
			4.5	_	2.1	1.35	_	1.35	V
			6.0	_	2.8	1.8	_	1.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -20 \mu A$	2.0	1.9	2.0	_	1.9	_	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -20 \mu A$	4.5	4.4	4.5	_	4.4	_	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -20 \mu A$	6.0	5.9	6.0	_	5.9	_	V
		$V_I = V_{IH}$ or $V_{IL}$ ; $I_O = -2.0$ mA	4.5	4.13	4.32	_	3.7	_	V
		$V_I = V_{IH}$ or $V_{IL}$ ; $I_O = -2.6$ mA	6.0	5.63	5.81	_	5.2	_	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 20 \mu\text{A}$	2.0	_	0	0.1	_	0.1	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 20 \mu\text{A}$	4.5	_	0	0.1	_	0.1	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 20 \mu\text{A}$	6.0	_	0	0.1	_	0.1	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 2.0 \text{ mA}$	4.5	_	0.15	0.33	_	0.4	V
		$V_I = V_{IH}$ or $V_{IL}$ ; $I_O = 2.6$ mA	6.0	_	0.16	0.33	-	0.4	V
ILI	input leakage current	$V_I = V_{CC}$ or GND	6.0	_	_	1.0	_	1.0	μΑ
Icc	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	6.0	_	_	10	_	20	μА

### Note

1. All typical values are measured at  $T_{amb}$  = 25 °C.

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### Family 74HCT1G

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

		TEST CONDI			T <sub>amb</sub> (°C	)			
SYMBOL	PARAMETER	OTHER	V 00	-	-40 to +8	5	-40 to	+125	UNIT
		OTHER	V <sub>CC</sub> (V)	MIN.	<b>TYP.</b> (1)	MAX.	MIN.	MAX.	
V <sub>IH</sub>	HIGH-level input voltage		4.5 to 5.5	2.0	1.6	_	2.0	_	V
V <sub>IL</sub>	LOW-level input voltage		4.5 to 5.5	_	1.2	0.8	_	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -20 \mu\text{A}$	4.5	4.4	4.5	_	4.4	_	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -2.0 \text{ mA}$	4.5	4.13	4.32	_	3.7	_	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 20 \mu A$	4.5	_	0	0.1	_	0.1	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 2.0 \text{ mA}$	4.5	_	0.15	0.33	_	0.4	V
I <sub>LI</sub>	input leakage current	$V_I = V_{CC}$ or GND	5.5	_	_	1.0	_	1.0	μΑ
I <sub>CC</sub>	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	_	_	10	_	20	μΑ
$\Delta I_{CC}$	additional supply current per input	$V_I = V_{CC} - 2.1 \text{ V};$ $I_O = 0$	4.5 to 5.5	_	_	500	_	850	μΑ

### Note

<sup>1.</sup> All typical values are measured at  $T_{amb}$  = 25  $^{\circ}\text{C}.$ 

# 2-input AND gate

74HC1G08; 74HCT1G08

### **AC CHARACTERISTICS**

### **Type 74HC1G08**

GND = 0 V;  $t_r = t_f \le 6.0$  ns;  $C_L = 50$  pF.

		TEST CONDITI							
SYMBOL PARAMETER		WAVEFORMS	W 00		40 to +8	5	−40 to	UNIT	
		WAVEFORING	IS V <sub>CC</sub> (V)	MIN.	<b>TYP.</b> <sup>(1)</sup>	MAX.	MIN.	MAX.	
t <sub>PHL</sub> /t <sub>PLH</sub>	propagation delay	see Figs 5 and 6	2.0	_	25	115	_	135	ns
	A and B to Y		4.5	_	9	23	_	27	ns
			6.0	_	8	20	_	23	ns

### Note

1. All typical values are measured at  $T_{amb}$  = 25 °C.

### Type 74HCT1G08

GND = 0 V;  $t_r = t_f \le 6.0$  ns;  $C_L = 50$  pF.

		TEST CONDITION							
SYMBOL	PARAMETER	WAVEFORMS	V 00	_	40 to +8	5	−40 to	+125	UNIT
		WAVEFORWS	V <sub>CC</sub> (V)	MIN.	<b>TYP.</b> <sup>(1)</sup>	MAX.	MIN.	MAX.	
t <sub>PHL</sub> /t <sub>PLH</sub>	propagation delay A and B to Y	see Figs 5 and 6	4.5	_	11	23	_	27	ns

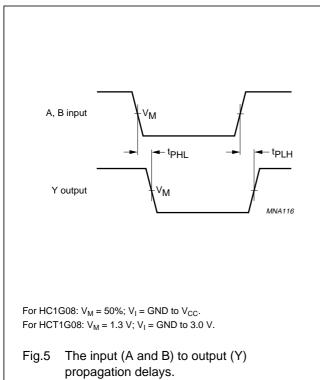
### Note

1. All typical values are measured at  $T_{amb}$  = 25 °C.

### 2-input AND gate

# 74HC1G08; 74HCT1G08

### **AC WAVEFORMS**



Definitions for test circuit:  $C_L = \text{Load capacitance including jig and probe capacitance} \\ (\text{See "AC characteristics"}). \\ R_T = \text{Termination resistance should be equal to the output impedance } Z_0 \text{ of the pulse generator.} \\ Fig. 6 \text{ Load circuitry for switching times.} \\$ 

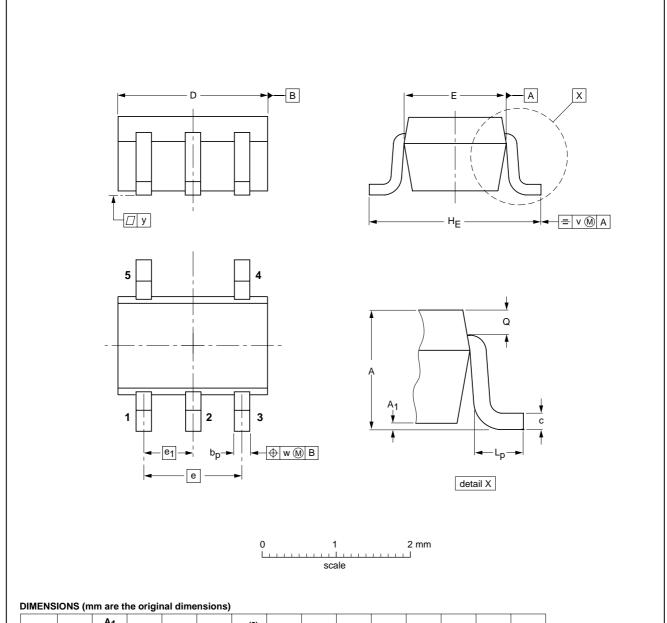
# 2-input AND gate

# 74HC1G08; 74HCT1G08

### **PACKAGE OUTLINES**

Plastic surface mounted package; 5 leads

**SOT353** 



UNIT	Α	A <sub>1</sub> max	bp	С	D	E <sup>(2)</sup>	е	e <sub>1</sub>	HE	Lp	Q	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

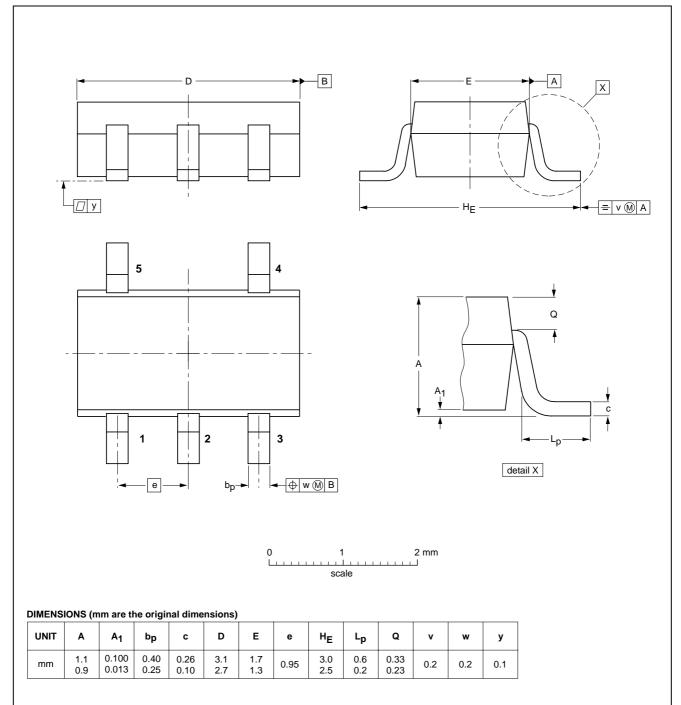
OUTLINE		REFER	ENCES	EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE	
SOT353			SC-88A		97-02-28	

# 2-input AND gate

# 74HC1G08; 74HCT1G08

### Plastic surface mounted package; 5 leads

**SOT753** 



OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT753			SC-74A			02-04-16

### 2-input AND gate

### 74HC1G08; 74HCT1G08

#### **SOLDERING**

### Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our "Data Handbook IC26; Integrated Circuit Packages" (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

### Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

#### Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

 For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

### Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

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### Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE <sup>(1)</sup>	SOLDERING METHOD		
PACKAGE	WAVE	REFLOW <sup>(2)</sup>	
BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA	not suitable	suitable	
HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable <sup>(3)</sup>	suitable	
PLCC <sup>(4)</sup> , SO, SOJ	suitable	suitable	
LQFP, QFP, TQFP	not recommended <sup>(4)(5)</sup>	suitable	
SSOP, TSSOP, VSO	not recommended <sup>(6)</sup>	suitable	

#### **Notes**

- 1. For more detailed information on the BGA packages refer to the "(LF)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- 4. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 5. Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- Wave soldering is suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

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#### **DATA SHEET STATUS**

DATA SHEET STATUS(1)	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification.  Supplementary data will be published at a later date. Philips  Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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#### **Notes**

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

### **DEFINITIONS**

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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NOTES

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NOTES

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